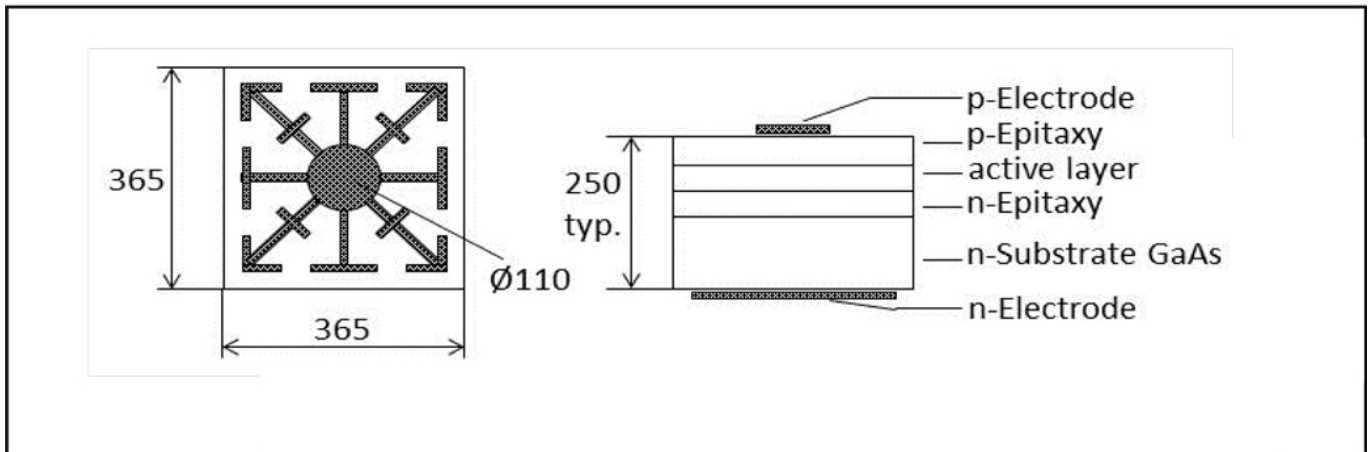




ELC-1020-17-1

Radiation	Type	Electrodes
Infrared	MQW / GaAs	P (anode) up



Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.25	1.45	V
Reverse current	$I_R = 5 \text{ V}$	I_R			10	μA
Output power	$I_F = 20 \text{ mA}$	Φ_e		3		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p		1020		nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		35		nm
Switching times	$I_F = 20 \text{ mA}$	t_r, t_f		15; 20		ns

¹ Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top



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